

# BRCS900P10DP

Rev.A Aug.-2023

## / Descriptions

TO-252 P MOS  
P-CHANNEL MOSFET in a TO-252 Plastic Package.

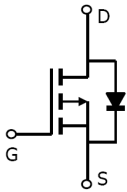
## / Features

$V_{DS}(V)=-100V$   $I_D=-18A$   
 $R_{DS(ON)}@-10V<90m$  (Typ.80mR)  
 $R_{DS(ON)}@-4.5V<100m$  (Typ.90mR)  
HF Product.

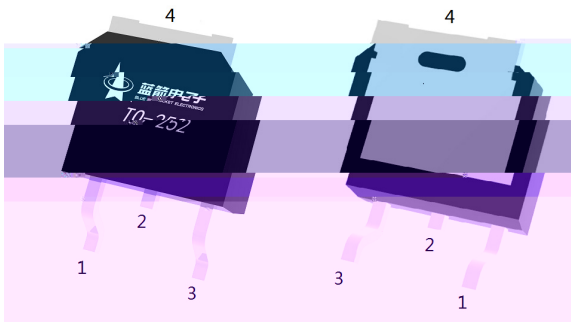
## / Applications

DC/DC  
Power Management of Industrial DC/DC Converter.

## / Equivalent Circuit



## / Pinning



PIN1 G      PIN 2 D      PIN 3 S      PIN 4 D

## / Marking

See Marking Instructions.

/ Absolute Maximum Ratings( $T_a=25$  )

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DS}$	-100	V
Drain Current - Continuous		$I_D(T_c=25)$	-18	A
Drain Current – Pulsed		$I_{DM}$	-54	A
Gate-Source Voltage		$V_{GS}$	$\pm 20$	V
Power Dissipation		$P_D(T_c=25)$	65	W
Single Pulse Avalanche Energy(L=0.5mH)		$E_{AS}$	185	mJ
Avalanche Current(L=0.5mH)		$I_{AS}$	-21.5	A
Junction and Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	
Thermal resistance, junction - ambient	Steady-State	$R_{JA}$	63	/ W
Thermal resistance, junction - case	Steady-State	$R_{JC}$	1.92	

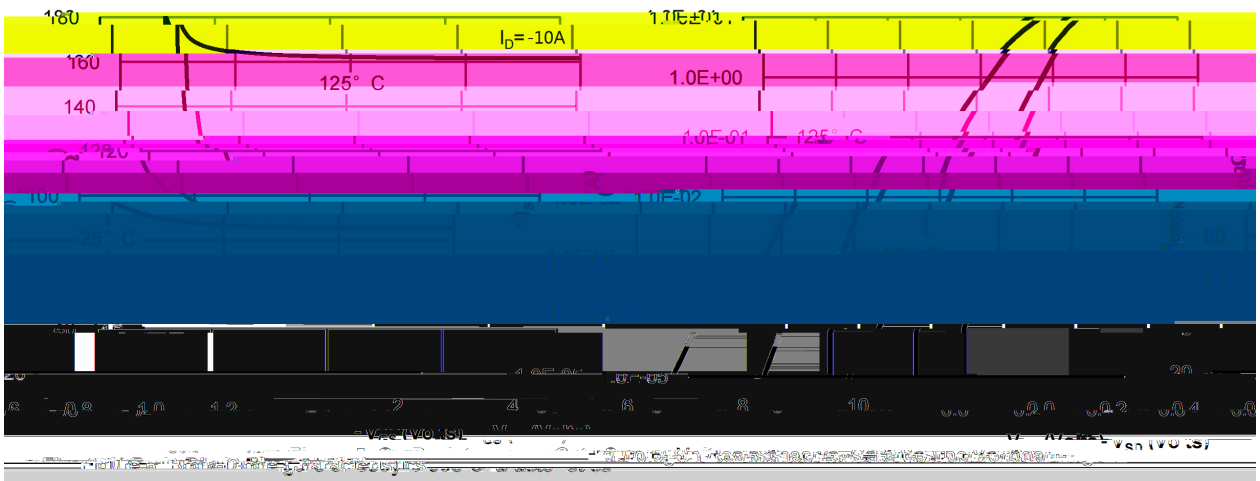
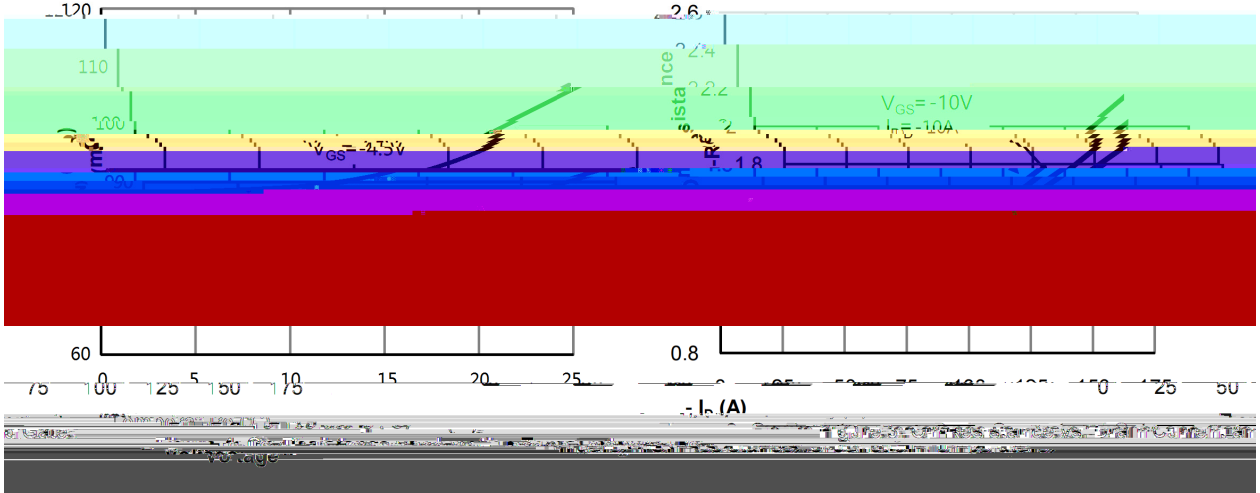
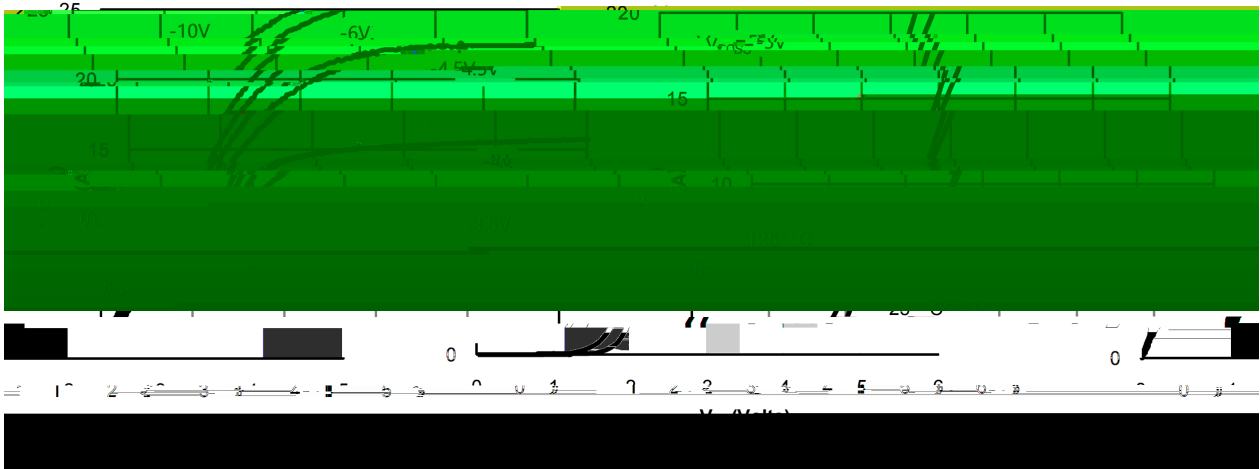
/ Electrical Characteristics( $T_a=25$  )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=-250$ A $V_{GS}=0V$	-100	-110		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-100V$ $V_{GS}=0V$			-1	$\mu A$
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250$ A	-1	-1.7	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-10A$		80	90	m
		$V_{GS}=-4.5V, I_D=-10A$		90	100	
Diode Forward Voltage	$V_{SD}$	$I_S=-1A, V_{GS}=0V$			-1.2	V
Input Capacitance	$C_{iss}$	$V_{DS}=-15V$ $V_{GS}=0V$ $f=1.0MHz$		5200		pF
Output Capacitance	$C_{oss}$			750		
Reverse Transfer Capacitance	$C_{rss}$			450		
Gate resistance	$R_g$	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		4.2		
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=-10V, V_{DS}=-50V,$ $I_D=-5A$		5.9		nC
Total Gate Charge	$Q_{g(4.5V)}$			2.7		
Gate Source Charge	$Q_{gs}$			1.2		
Gate Drain Charge	$Q_{gd}$			1.2		

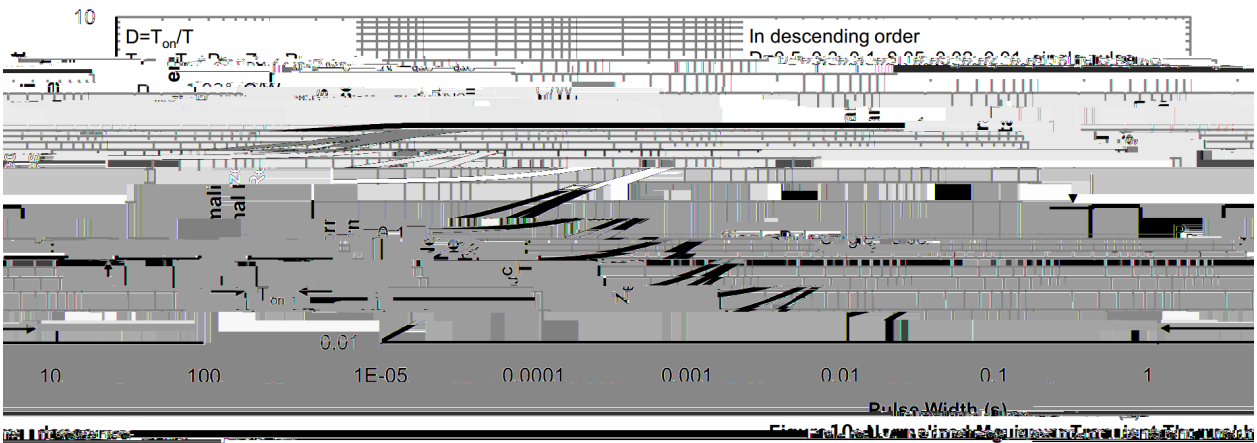
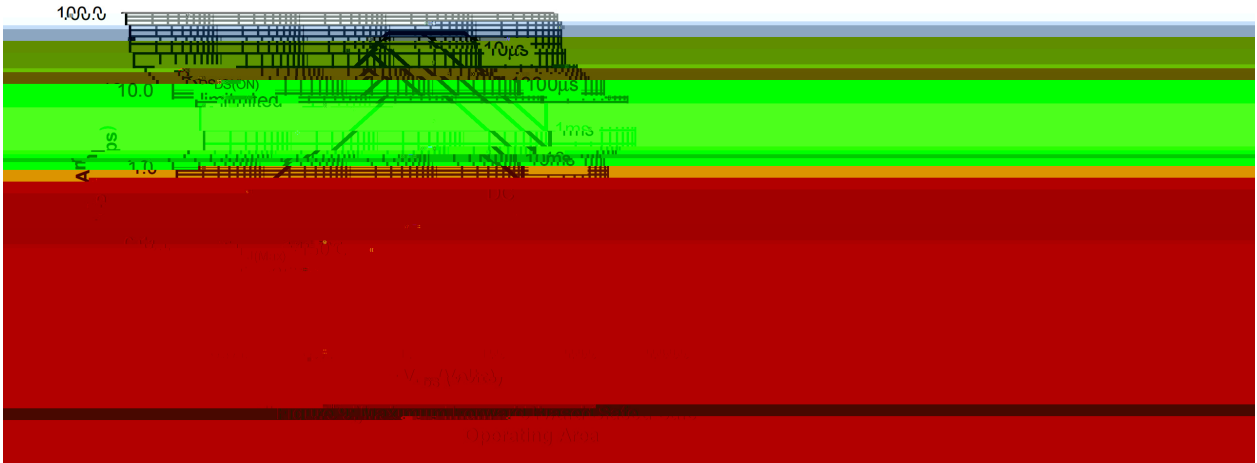
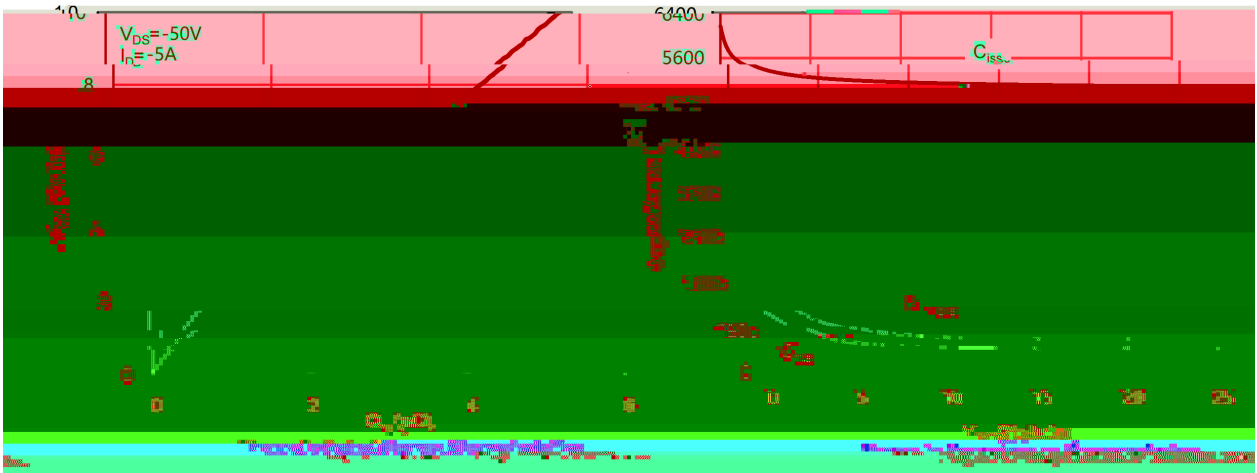
Parameter

@  $f$

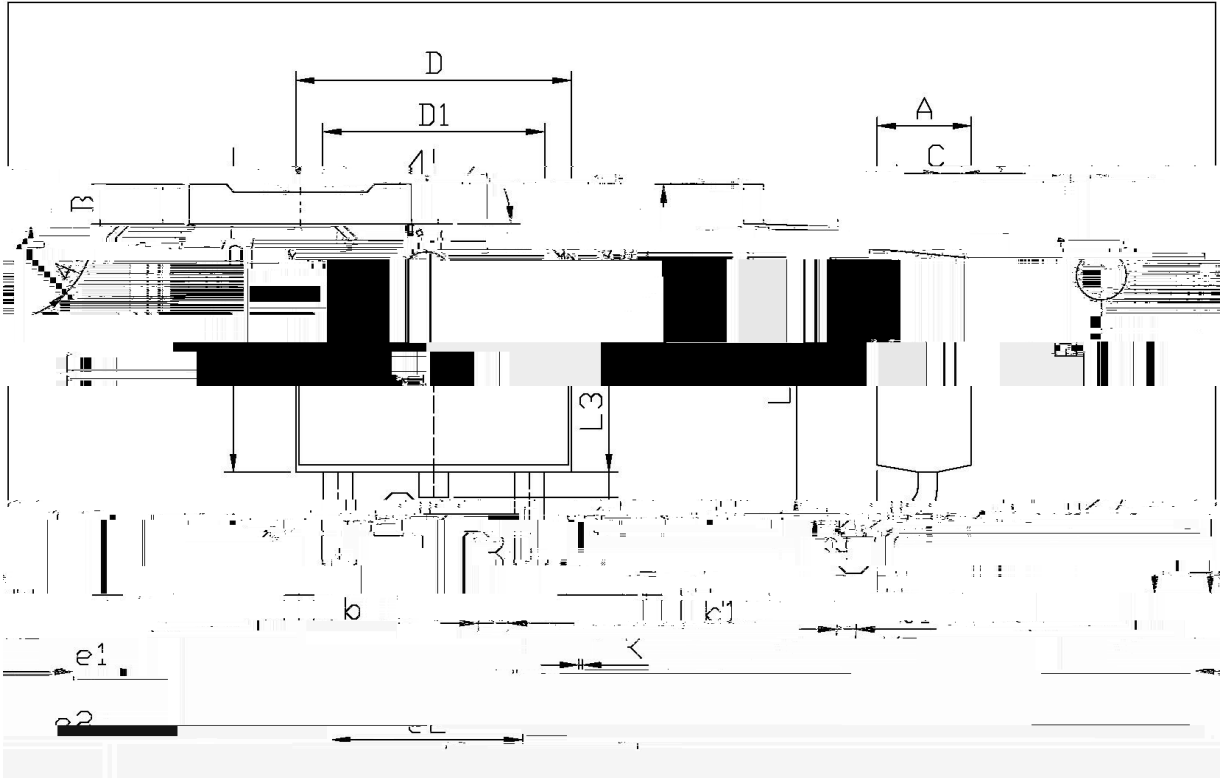
/ Electrical Characteristic Curve



/ Electrical Characteristic Curve



**/ Package Dimensions**

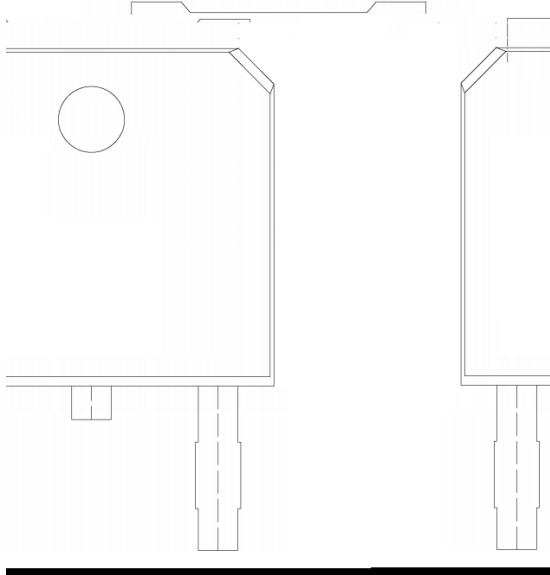


单位: mm

Dimensions, Millimeters		Dimensions, In Millimeters	
Symbol	Min	Max	Symbol
e1	2.27	2.34	e1
b	0.70	0.70	b
L3	0.75	0.55	L3
$\phi$	0.10	0.10	$\phi$
D1	5.10	5.50	D1
D	6.25	6.75	D
A	1.25	1.25	A
C	0.95	0.95	C
B	0.75	0.75	B
k1	0.55	0.55	k1
<math>\phi</math>	0.50	0.50	<math>\phi</math>

T0-252

**/ Marking Instructions**



BR  
900P10  
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( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)